GBAV152

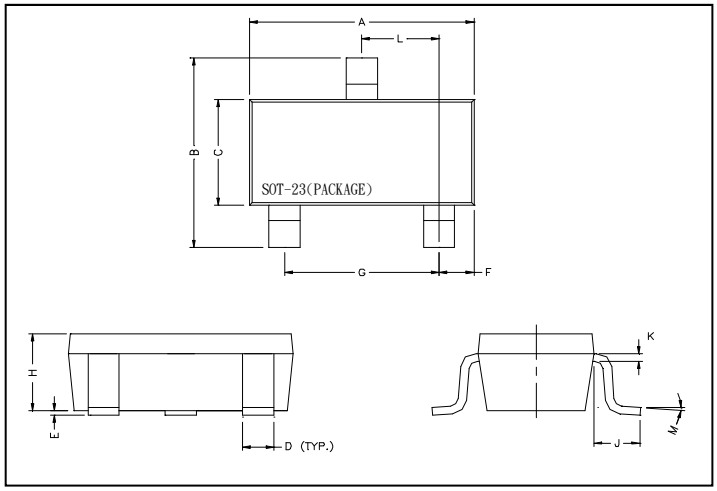
SURFACE MOUNT, SWITCHING DIODE

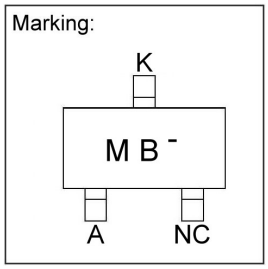
VOLTAGE 80V, CURRENT 0.1A

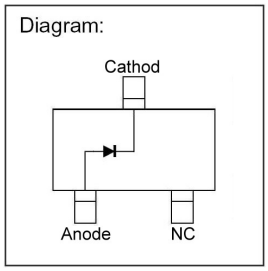
Description

The GBAV152 is designed for ultra high speed switching application.

Package Dimensions







REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings (At T_A = 25℃ unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Max. Peak Reverse Voltage	V_{RM}	80	V
Max. Reverse Voltage	V_R	80	V
Max. Average Forward Rectified Current	Io	100	mA
Non-Repetitive Peak Forward surge Current @Tp =1.0us	I_{FSM}	225	mA
@Tp =1.0s		500	
Power Dissipation	PD	225	mW
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55 ~ +150	℃

Electrical Characteristics (At T_A = 25℃ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	$V_{(BR)R}$	80	-	V	I_R=100μA
Forward Voltage	V_F	-	1.2	V	I_F=100mA
Reverse Voltage Leakage Current	I_R	-	100	nA	V_R=75V
Diode Capacitance	C_D	-	2.0	pF	V_R=0V, f=1.0MHz
Reverse Recovery Time (Figure 1)	t_{rr}	-	3.0	ns	I_F=10mA, V_R=6V, R_L=100Ω, I_{rr}=0.1I_R

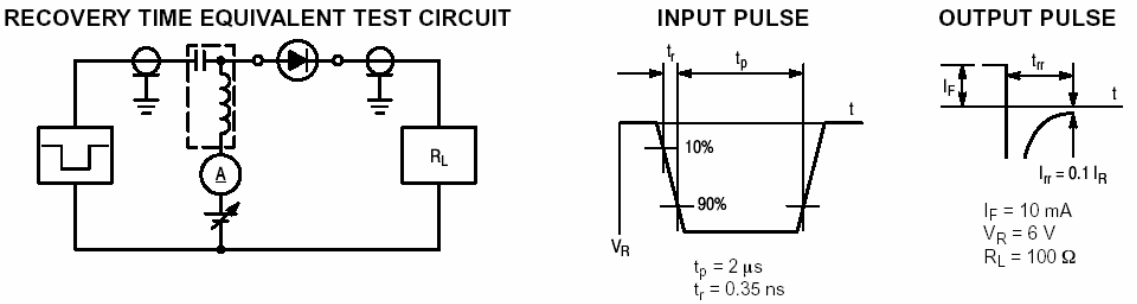


Figure 1. Reverse Recovery Time Equivalent Test Circuit

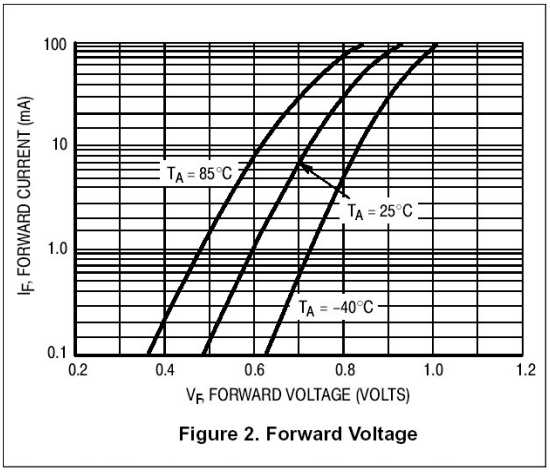


Figure 2. Forward Voltage

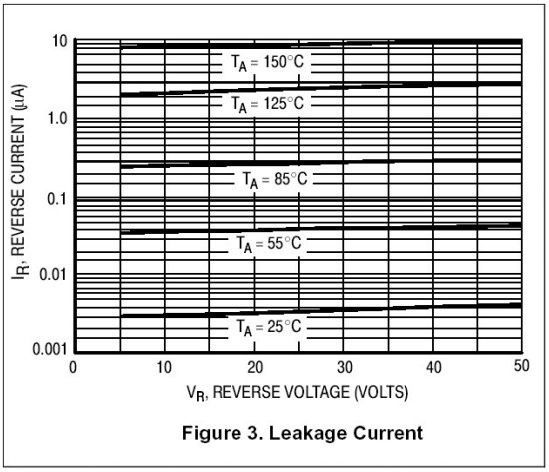


Figure 3. Leakage Current

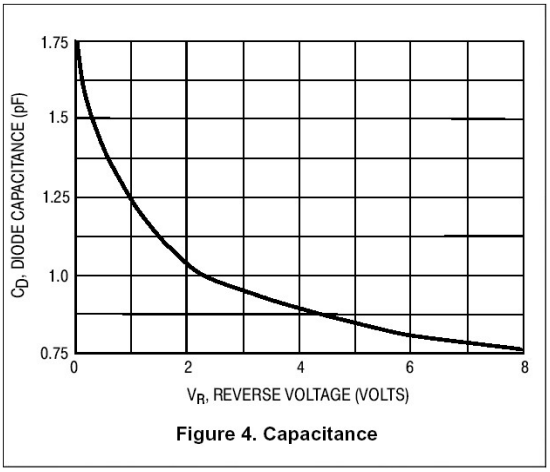


Figure 4. Capacitance

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